

# Si858x Data Sheet

# Integrated Isolated RS-485 Transceivers

The Si858x products are devices that combine robust fully compliant RS-485 transceivers with signal isolation. These devices are ideal for industrial automation applications that require isolated interfaces for FieldBus systems that form a communication network for connecting sensors, actuators, and controllers.

These devices are ideal for isolating nodes on FieldBuses based on the RS-485 standard such as ProfiBus or ModBus. These transmission lines can be susceptible to electrical noise transients especially in harsh environments such as a factory floor, or in sensitive environments such as process control or data acquisition. Isolation provides a means of protection from such transients and noise that could corrupt signal integrity.

These isolated transceivers can operate with a 3.3~V or 5.0~V nominal power supply and have robust bus fault tolerance of up-to  $\pm 30~V$  for protecting against harmful transients in the noisy environment where such systems are often utilized. The bus pins are also protected up to 15~kV HBM ESD. Product options are available for half duplex and full duplex mode in industry standard footprints and incorporate slew rate controlled drivers with 1~M Mbps data rate capability for reducing the EMI profile or options for high data rate up to 10~M Mbps with no slew rate control implemented. These products also offer safety and protection features such as receiver fail-safe and thermal protection.

These devices utilize Skyworks' proprietary silicon isolation technology, supporting up to 5 kVRMS (for 1 minute) isolation voltage per UL 1577. This technology enables high CMTI (>60 kV/µs), low propagation delays and skew, reduced variation with temperature, and age and tight part-to-part matching.

# **Industrial Applications**

- · Industrial automation systems
- · Isolated switch mode supplies
- · Inverters
- · Data acquisition
- Motor control
- · PLCs, distributed control systems

# Safety Approval

- · UL 1577 recognized
  - Up to 5000 V<sub>RMS</sub> for 1 minute
- · CSA certification conformity
  - IEC 62368-1 (reinforced insulation)

#### **KEY FEATURES**

- Compliance to TIA/EIA-485-A (RS-485), EN 50170 (ProfiBus)
- Industry standard footprint and logic operation
- · Signaling rates of up to 10 Mbps
- · HBM 15 kV bus pin ESD ratings
- Common mode voltage supported for operation: –7 V to +12 V
- Bus fault protection: ±30 V
- · Thermal shutdown protection
- VDD1: 3.0 to 5.5 V
- VDD2: 3.3 V or 5.0 V
- · 50 ns typical driver propagation delay
- 5 kV isolation UL 1577, CSA, and CQC certified
- CMTI of 100 kV/µs (min)
- Unit loading: Up to 256 transceivers on a bus at 5 V, 128 at 3.3 V
- T<sub>A</sub>: -40 to +125 °C
- JEDEC-qualified
- · WB SOIC-16 RoHS-compliant package

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# 1. Ordering Guide

Table 1.1. Ordering Guide

See Top Marking for product name decoder.

Ordering Part Number (OPN)	RS-485 Configuration	Nodes	Slew Rate Control	Data Rate (Mbps)	VDD2 (V)	Isolation Rating (kVrms)
Si85853D-IS	Half Duplex	64	Yes	1	5.0	5.0
Si85833D-IS	Half Duplex	64	Yes	1	3.3	5.0
Si85855D-IS	Half Duplex	256	No	10	5.0	5.0
Si85835D-IS	Half Duplex	256	No	10	3.3	5.0
Si85856D-IS	Half Duplex with isolated Tx_EN pin	256	No	10	5.0	5.0
Si85836D-IS	Half Duplex with isolated Tx_EN pin	256	No	10	3.3	5.0
Si85857D-IS	Full Duplex	64	Yes	1	5.0	5.0
Si85837D-IS	Full Duplex	64	Yes	1	3.3	5.0
Si85858D-IS	Full Duplex	256	No	10	5.0	5.0
Si85838D-IS	Full Duplex	256	No	10	3.3	5.0

- 1. All packages are RoHS-compliant with peak reflow temperatures of 260 °C according to the JEDEC industry standard classifications and peak solder temperatures.
- 2. "Si" and "SI" are used interchangeably.
- 3. An "R" at the end of the part number denotes tape and reel packaging option.
- 4. The temperature ranges is -40 to +125 °C.

# 2. Functional Description

# 2.1 Theory of Operation

The Si858x family of products is capable of transmitting and receiving RS-485 signals from one power domain to an isolated domain with up to 5.0 kVrms of isolation. In addition, these products include a completely integrated RS-485 transceiver.

# 2.2 Digital Isolation

The operation of an Si858x digital channel is analogous to that of a digital buffer, except an RF carrier transmits data across the isolation barrier. This simple architecture provides a robust isolated data path and requires no special considerations or initialization at start- up. A simplified block diagram for a single Si858x channel is shown in the following figure.

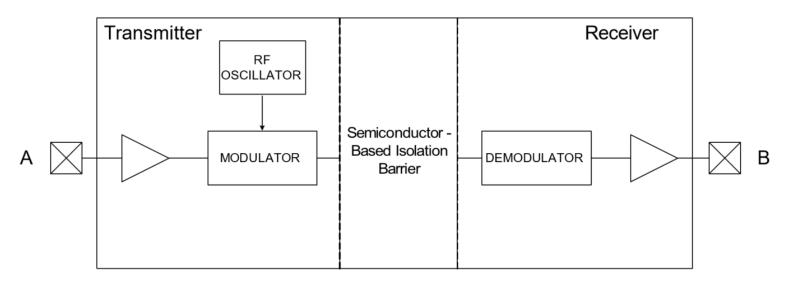


Figure 2.1. Simplified Si858x Channel Diagram

A channel consists of an RF transmitter and RF receiver separated by a silicon dioxide capacitive isolation barrier. In the transmitter, input A modulates the carrier provided by an RF oscillator using on/off keying. The receiver contains a demodulator that decodes the input state according to its RF energy content and applies the result to output B via the output driver. This RF on/off keying scheme is superior to pulse code schemes as it provides best-in-class noise immunity, low power consumption, and better immunity to magnetic fields. See the following figure for more details.

Figure 2.2. Modulation Scheme

Input Signal

Modulation Signal

Output Signal

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#### 2.3 RS-485 Signaling

These isolated transceivers are compliant to the TIA/EIA-485 standard. They are available in full duplex as well as half duplex configurations.

For the driver operation, when VDD1 and VDD2 are both powered up and the driver enabled (Tx\_EN pin is high), a logic high on driver input pin Tx produces a corresponding logic high on the isolated driver output bus pin Y (pin A for half duplex) and a logic low on pin Z (pin B for half duplex). A logic low on the Tx pin will invert the outputs. Thus, the differential output voltage on the bus, defined as VOD = VY/A – VB/Z, is positive when Tx is high and negative when Tx is low. The Tx\_EN pin is active high with a pull-up resistor internally, driving it low will disable the driver function and the bus pins will be high impedance.

The receiver enable is active low with an internal pull-down resistor. Leaving it open or driving it low enables the receiver while driving it high will disable it. With the receiver enabled, a differential input (defined as VID = VA-VB) greater than the input threshold of the receiver produces a logic high on the receiver output pin Rx. A differential input that is lower than the receiver threshold will produce a logic low.

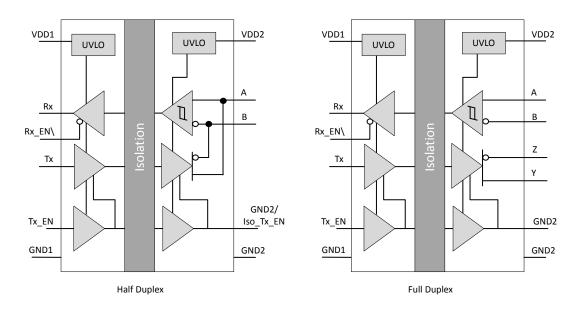


Figure 2.3. Isolated Transceiver Block Diagram

# 3. Device Operation

Table 3.1. Si858x Driver Operation

Input TX <sup>1</sup>	Enable TX_EN <sup>1</sup>	VDD1 <sup>2, 3</sup>	VDD2 <sup>2, 3</sup>	Output ISO_TX_EN <sup>1</sup>	Output Y or A <sup>1</sup>	Output Z or B <sup>1</sup>
Н	Н	Р	Р	Н	Н	L
L	Н	Р	Р	Н	L	Н
Х	L	Р	Р	L	Hi-Z	Hi-Z
Х	OPEN	Р	Р	L	Hi-Z	Hi-Z
OPEN	Н	Р	Р	Н	L	Н
X <sup>4</sup>	Х	UP <sup>5</sup>	Р	L	Hi-Z	Hi-Z
Х	X	Р	UP <sup>6</sup>	UD	UD	UD
Х	X	UP	UP	UD	UD	UD

- 1. X = not applicable; H = Logic High; L = Logic Low; Hi-Z = High Impedance, UD = undetermined.
- 2. VDD1 and VDD2 are the logic and transceiver side power supplies.
- 3. "Powered" state (P) is defined as > 2.5 V, "Unpowered" state (UP) is defined as VDD = 0 V.
- 4. Note that an I/O can power the die for a given side through an internal diode if its source has adequate current.
- 5. For reliability reasons, it is highly recommended that the power supply (VDD1 or VDD2) not be powered down while TX\_EN is asserted high or while it is in the transition to disable state.
- 6. When VDD2 is UP, ISO\_Tx\_EN pin may still follow the TX\_EN state. It is recommended that while VDD2 is in the UP state, the status of ISO\_TX\_EN be ignored.

Table 3.2. Si858x Receiver Operation

Differential Input VID = VIA – VIB <sup>1</sup>	Enable RX_EN\ <sup>2</sup>	VDD1 <sup>3, 4</sup>	VDD2 <sup>3, 4</sup>	Output RX <sup>2</sup>
VID ≥ –10mV	L or OPEN	Р	Р	Н
-200 mV < VID < -10 mV	L or OPEN	Р	Р	UD
VID ≤ –200 mV	L or OPEN	Р	Р	L
X	Н	Р	Р	Hi-Z
OPEN	L	Р	Р	Н
SHORT	L	Р	Р	Н
IDLE (terminated)	L	Р	Р	Н
Х	X <sup>5</sup>	UP	Р	UD
X	L or open	Р	UP	Н
Х	Н	Р	UP	Hi-Z

- 1. Open = transceiver disconnected from bus, Short = bus shorted, Idle = bus not actively driven.
- 2. X = not applicable; H = Logic High; L = Logic Low; Hi-Z = High Impedance, UD = undetermined.
- 3. VDD1 and VDD2 are the logic and transceiver side power supplies.
- 4. "Powered" state (P) is defined as > 2.5 V, "Unpowered" state (UP) is defined as VDD = 0 V.
- 5. Note that an I/O can power the die for a given side through an internal diode if its source has adequate current.

# 4. Electrical Specifications

**Table 4.1. Recommended Operating Conditions** 

Parameter	Symbol	Min	Тур	Max	Unit
Ambient Operating Temperature <sup>1</sup>	T <sub>A</sub>	-40	25	125	°C
Logic Supply Voltage	VDD1	2.5	_	5.5	V
Transceiver Supply Voltage	VDD2	3.135 4.75	3.3 5.0	3.465 5.25	V
Voltage on Bus Pin A, B, Y, Z	V <sub>CM</sub>	-7	_	12	V
High Level Input voltage on Tx, TX_EN, Rx_EN\	V <sub>IH</sub>	0.7 x VDD1			V
Low Level Input Voltage	V <sub>IL</sub>	_	_	0.3 x VDD1	V
Differential Input Voltage	V <sub>ID</sub>	-5	_	10	V
Differential Load Resistance	$R_D$	54			Ω
Driver Output Current	I <sub>OD</sub>	-60		60	mA
Receiver Output Current	I <sub>OR</sub>	-4		4	mA

#### Note:

**Table 4.2. Electrical Characteristics** 

Typical specs at 25  $^{\circ}$ C, with VDD1 = VDD2 = 5.0 V, unless specified, -40  $^{\circ}$ C to 125  $^{\circ}$ C ambient temperature.

Parameter	Symbol	Test (	Condition	Min	Тур	Max	Unit
		Supply Cu	ırrent				
		VDD1 = 3.3 V	Tx_EN = 0	_			mA
			Tx_EN = 1 , 1 Mbps	_			
Comple Comment VDD4	IDD4		Tx_EN = 1 , 10 Mbps	_			
Supply Current, VDD1	IDD1	VDD1 = 5.0 V	Tx_EN = 0	_			
			Tx_EN = 1 , 1 Mbps	_	3.7	5.2	
			Tx_EN = 1 , 10 Mbps	_	19	24	
		VDD2 = 3.3 V	Tx_EN = 0	_	19.5		
			Tx_EN = 1 , 1 Mbps	_	58	5.2	
0 0 1.1/DD0	IDDO		Tx_EN = 1 , 10 Mbps	_	69		
Supply Current, VDD2	IDD2	VDD2 = 5.0 V	Tx_EN = 0	_	19.5		mA
			Tx_EN = 1 , 1 Mbps	_	72	79	
			Tx_EN = 1 , 10 Mbps		92	110	mA
Driver	1		1				

<sup>1.</sup> The maximum ambient temperature is dependent on data frequency, output loading, number of operating channels, and supply voltage.

Differential Output Voltage   VOD(SS)   RLOAD = 54 Ω   Figure 4.1 Measurement for Driver Differential Color on page 11   1.5     VDD2   V   V   V   V   V   V   V   V   V	Parameter	Symbol	Test C	ondition	Min	Тур	Max	Unit
Change in Differential Output Voltage   VOD(SS)   RLOAD = 54 Ω   Voltage VOD with Load on page 11   1.5     VDD2   V		VOD(SS)	RLOAD = 54 Ω	for Driver Differential Voltage, VOD with Load	1.5	_	VDD2	V
Open Circuit Differential Output Voltage Under/Overshoot         VOD         No load         for Driver Differential Voltage VOD, No Load on page 11         1.5         — VDD2         V DD2         V DIG			RLOAD = 54 Ω	for Driver Differential Voltage, VOD with Load	-200.0	_	200.0	mV
Differential Output Voltage Under/Overshoot   VOD(RING)   RLOAD = 54 Ω   Interest Differential Voltage, VOD with Load on page 11   VOD(RING)   VOD(		VOD	No load	for Driver Differential Voltage VOD, No Load	1.5	_	VDD2	V
Common Mode Output Voltage Steady State		VOD(RING)	RLOAD = 54 Ω	for Driver Differential Voltage, VOD with Load	_	_	1	V
Common Mode Output Voltage Steady State     VOC(SS)     VDD2 = 5.0 V RLOAD = 54 Ω     Figure 4.3 Measurement for Driver Common-Mode Voltage VOC on page 12     -200     —     200     mV       Peak-to-Peak Common Mode Output Voltage Steady State Output Voltage     VOC(PP)     VDD2 = 5.0 V RLOAD = 54 Ω     Figure 4.3 Measurement for Driver Common-Mode Voltage VOC on page 12     —     500     —     mV       Short Circuit Steady State Output Current     IOS(SS)     Tx_EN = 1     Figure 4.3 Measurement for Driver Common-Mode Voltage VOC on page 12     —     500     —     mV       Receiver       Positive Going Differential Input Threshold Voltage Not Driver Differential Input Threshold Voltage Not Driver Differential Input Threshold Voltage Not Driver Driver Differential Input Threshold Voltage Not Driver Driv		VOC(SS)		for Driver Common Mode Voltage VOC on page	2	2.1	3	V
Change in Common Mode Output Voltage Steady State		VOC(SS)		for Driver Common-Mode Voltage VOC on page				
Peak-to-Peak Common Mode Output Voltage       VOC(PP)       VDD2 = 5.0 V RLOAD = 54 Ω       for Driver Common-Mode Voltage VOC on page 12       — 500       — mV         Short Circuit Steady State Output Current       IOS(SS)       Tx_EN = 1       Figure 4.1 Measurement for Driver Differential Voltage, VOD with Load on page 11       -250       — +250       mA         Receiver         Positive Going Differential Input Threshold Voltage       VIT+       IO = -8 mA       -85-       -75       -66       mV         Negative Going Differential Input Threshold Voltage       VIT-       IO = 8 mA       -137       -135       -123       mV         Input Hysteresis Voltage       V(HYS)       49       50       63       mV         Differential Input Capacitance       CID       Test signal is 1.5 MHz sine wave with 1 Vpp magnitude, CID measured across A and B (or Y and Z)       — 7       10       pF         Single Ended Input Resistance       RA, RB       Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11       96       127       223       kΩ				for Driver Common-Mode Voltage VOC on page	-200	_	200	mV
Short Circuit Steady State Output Current  IOS(SS)  Tx_EN = 1  Figure 4.1 Measurement for Driver Differential Voltage, VOD with Load on page 11  Positive Going Differential Input Threshold Voltage  VIT+  IO = -8 mA  Negative Going Differential Input Threshold Voltage  VIT- IO = 8 mA  Input Hysteresis Voltage  V(HYS)  Differential Input Capacitance  CID  Test signal is 1.5 MHz sine wave with 1 Vpp magnitude, CID measured across A and B (or Y and Z)  Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11  Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11	1	VOC(PP)		for Driver Common-Mode Voltage VOC on page	_	500	-	mV
Positive Going Differential Input Threshold Voltage       VIT+       IO = -8 mA       -85-       -75       -66       mV         Negative Going Differential Input Threshold Voltage       VIT-       IO = 8 mA       -137       -135       -123       mV         Input Hysteresis Voltage       V(HYS)       49       50       63       mV         Differential Input Capacitance       CID       Test signal is 1.5 MHz sine wave with 1 Vpp magnitude, CID measured across A and B (or Y and Z)       -       7       10       pF         Single Ended Input Resistance       RA, RB       Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11       96       127       223       kΩ		IOS(SS)	Tx_EN = 1	Figure 4.1 Measurement for Driver Differential Voltage, VOD with Load	-250	_	+250	mA
put Threshold VoltageVIT+IO = -8 mA-8575-66IIIVNegative Going Differential Input Threshold VoltageVIT-IO = 8 mA-137-135-123mVInput Hysteresis VoltageV(HYS)495063mVDifferential Input CapacitanceCIDTest signal is 1.5 MHz sine wave with 1 Vpp magnitude, CID measured across A and B (or Y and Z)-710pFSingle Ended Input ResistanceRA, RBFigure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 1196127223kΩ	Receiver							
Input Threshold Voltage  Input Hysteresis Voltage  V(HYS)  V(HYS)  Test signal is 1.5 MHz sine wave with 1 Vpp magnitude, CID measured across A and B (or Y and Z)  Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11  NO 63 mV  Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11		VIT+	IO = -8 mA		-85-	-75	-66	mV
Differential Input Capacitance  CID  Test signal is 1.5 MHz sine wave with 1 Vpp magnitude, CID measured across A and B (or Y and Z)  Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11  PF  10  pF		VIT-	IO = 8 mA		-137	-135	-123	mV
Single Ended Input Resistance  RA, RB  RA, RB  RA, RB  RA, RB  RA, RB  Lude, CID measured across A and B (or Y and Z)  Figure 4.2 Measurement for Driver Differential Voltage VOD, No Load on page 11  PF  10  PF  127  223  kΩ	Input Hysteresis Voltage	V(HYS)			49	50	63	mV
Single Ended Input Resistance  RA, RB  RA, RB  For Driver Differential Voltage VOD, No Load on page 11  Physical RA (No. 127) 223 (No. 127) 2	Differential Input Capacitance	CID			_	7	10	pF
Differential Input Resistance RID " 191 311 439 $k\Omega$		RA, RB		for Driver Differential Voltage VOD, No Load	96	127	223	kΩ
	Differential Input Resistance	RID		u	191	311	439	kΩ

Parameter	Symbol	Test C	ondition	Min	Тур	Max	Unit
Input Resistance Matching			tt.	-0.3		0.3	%
			VDD1 = 5.0 V,	VDD1-			
High Level Output Voltage:	VOH	VID = 200 mV	IOH = -4 mA	0.4	_	_	V
RX			VDD1 = 5.0 V	VDD1-			
			IOH = -20 uA	0.1	_	_	V
	VOL	VID = -200 mV	VDD1 = 5.0 V, IOL = 4 mA	_	_	0.4	V
Low Level Output Voltage: RX			VDD1 = 5.0 V, IOL = 20 uA	_	_	0.1	V
Bus Input Current	IA, IB	VI = -1	2 to 12 V	-200	_	200	uA
Other IO	1						
Low Level Input Current: TX RX_EN, STB	K, TX_EN,			_	_	15	uA
High Level Input Current: TX RX_EN, STB	X, TX_EN,			-15	_	_	uA
Input Leakage, Low or High	for V5_EN						
Input Voltage Hysteresis	VI(HYS)					150	mV
Switching Characteristics	1						
Maximum Data rate				_	_	10	Mbps
Driver							
		VDD2 = 5.0 V, RL = 54 0	O, CL = 50 pF, 50% to 50%				
Propagation Delay	tpLH, tpHL		for Driver Timing Chractern page 12	33	37	42	ns
			= 54 Ω. CL = 50 pF, 10% to				
Differential Signal Rise/Fall Time	tr, tf	Figure 4.4 Measurement	0% for Driver Timing Chracter- n page 12	30	34	38	ns
Pulse Skew (tpHL-tpLH)	tpsk	VDD2 = 5.0 V, RL = 54 0	Ω, CL = 50 pF, 50% to 50%	_	2	5	ns
	tp(A/BZH),	50% TX_EN=0,1 t	o 50% A,B transition				
Driver Enable/Disable Delay Time	tp(A/BZL), tp(A/BHZ), tp(A/BLZ)		le Delay Measurements on ge 13	_	40	108	ns
CMTI				60	100	_	kV/uS
Receiver		<u>I</u>					
		VDD2	! = 5.0 V				
Propagation Delay	tpLH, tpHL		nt for Receiver Output and eristics on page 12	_	38	43	ns
Pulse Skew (tpHL-tpLH)	tpsk						
Rx Output Rise/Fall Time	tr, tf	VDD1 = 5.0 V, CL	= 15 pF, 10% to 90%	_	3.7	4	ns
Receiver Enable/Disable De- lay Time	tp(ZH), tp(ZL), tp(HZ), tp(LZ)	VDD1,2 = 5.0	) V, CL = 15 pF	_	2	12	ns

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Delay from VDD2 Power Loss to RX=1			_	_	6	uS
Protection						
VDD1 Undervoltage Threshold	VDD <sub>UV+</sub>		1.9	2.2	2.4	V
VDD Undervoltage Threshold	VDD <sub>UV</sub>	V <sub>DD1</sub> rising	1.8	2.1	2.3	V
VDD1 Undervoltage Hysteresis			50	70	95	mV
VDD2 Undervoltage Thresh- old (5.0 V VDD2)	VDD2 <sub>UV+</sub>	V <sub>DD1</sub> rising	3.8	4.2	4.4	V
VDD2 Undervoltage Thresh- old (5.0 V VDD2)	VDD2 <sub>UV-</sub>	V <sub>DD2</sub> falling	3.8	4.1	4.4	V
VDD2 Undervoltage Hysteresis (5.0 V VDD2)			130	135	140	mV
VDD2 Undervoltage Threshold (3.3 V VDD2)	VDD2 <sub>UV+</sub>	V <sub>DD1</sub> rising	2.2	2.3	2.5	V
VDD2 Undervoltage Threshold (3.3 V VDD2)	VDD2 <sub>UV-</sub>	V <sub>DD2</sub> falling	2.2	4.1	2.5	V
VDD2 Undervoltage Hysteresis			63	65	68	mV

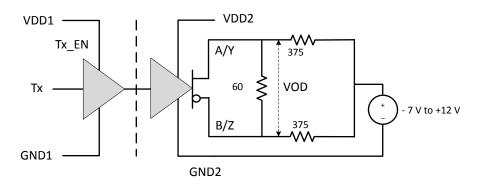


Figure 4.1. Measurement for Driver Differential Voltage, VOD with Load

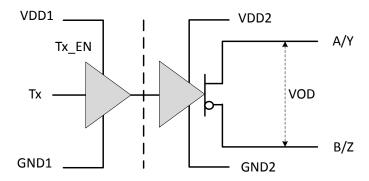


Figure 4.2. Measurement for Driver Differential Voltage VOD, No Load

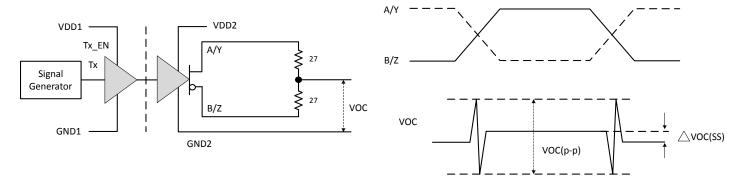


Figure 4.3. Measurement for Driver Common-Mode Voltage VOC

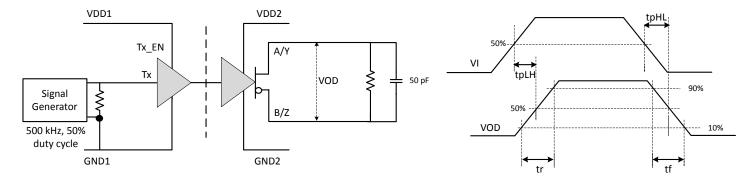


Figure 4.4. Measurement for Driver Timing Chracteristics

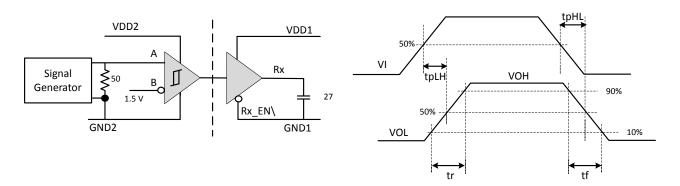


Figure 4.5. Measurement for Receiver Output and Timing Characteristics

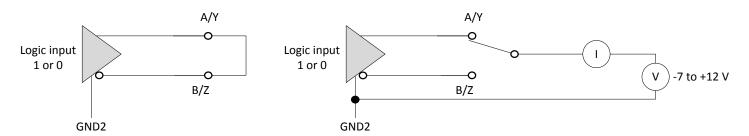


Figure 4.6. Short Circuit Current Measurement

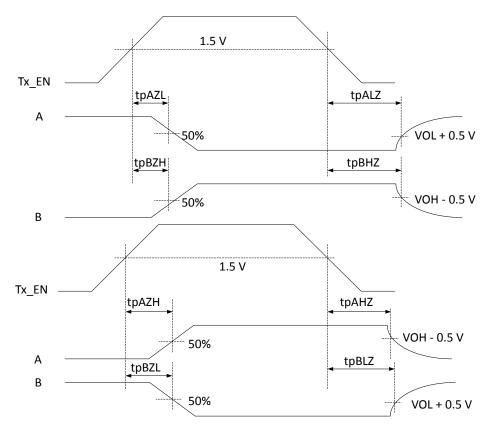
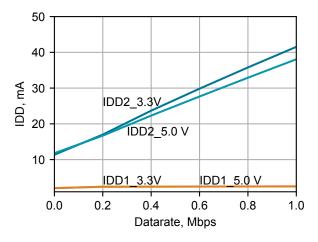


Figure 4.7. Enable/Disable Delay Measurements

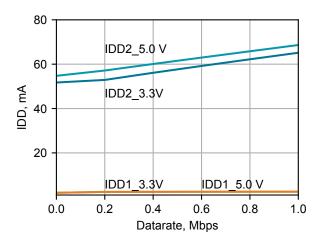
## **Typical Performance Characteristics**

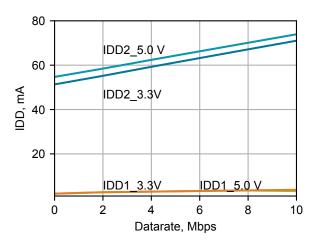


40 30 IDD2 5.0 V IDD, mA 20 IDD2\_3.3V 10 IDD1 5.0 V IDD1 3.3V 0 2 4 6 8 10 Datarate, Mbps

Figure 4.8. Si858x3/7 Supply Current vs. Data Rate, No Load

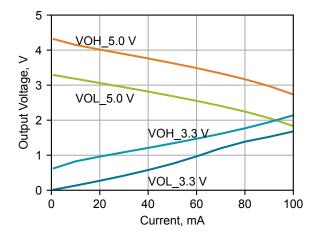
Figure 4.9. Si858x5/6/8 Supply Current vs. Data Rate, No Load





pF Load

Figure 4.10. Si858x3/7 Supply Current vs. Data Rate, 54 Ω, 50 Figure 4.11. Si858x5/6/8 Supply Current vs. Data Rate, 54 Ω, 50 pF Load



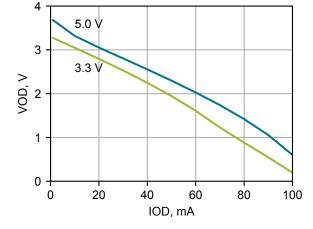
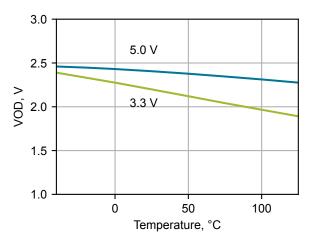


Figure 4.12. Driver Output Voltage vs. Current

Figure 4.13. Driver Differential Output Voltage vs. Current



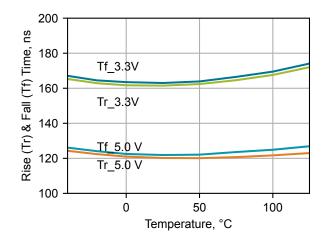
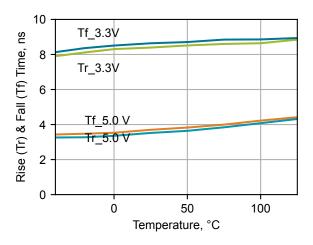


Figure 4.14. Driver Differential Output Voltage vs. Temperature

Figure 4.15. Si858x3/7 Driver Rise/Fall Time vs. Temperature



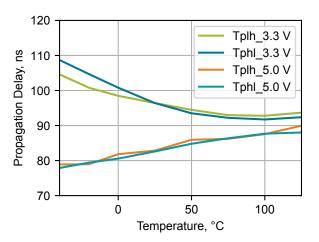
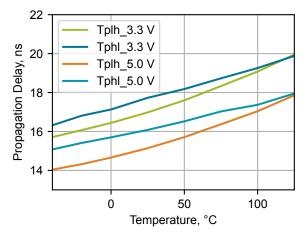


Figure 4.16. Si858x5/6/8 Driver Rise/Fall Time vs. Temperature

Figure 4.17. Si858x3/7 Driver Propagation Delay vs. Temperature



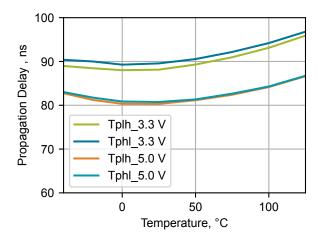


Figure 4.18. Si858x5/6/8 Driver Propagation Delay vs. Temperature

Figure 4.19. Receiver Propagation Delay vs. Temperature

# Table 4.3. Regulatory Information<sup>1</sup>

#### CSA

The Si858x is certified under CSA. For more details, see Master Contract Number 232873.

62368-1: Up to 600  $V_{RMS}$  reinforced insulation working voltage; up to 1000  $V_{RMS}$  basic insulation working voltage.

60601-1: Up to 250 V<sub>RMS</sub> working voltage and 2 MOPP (Means of Patient Protection).

#### **VDE**

The Si858x is certified under VDE. For more details, see File 5006301.

IEC60747-17: Up to 2121 Vpeak for reinforced insulation working voltage.

62368-1: Up to 600 V<sub>RMS</sub> reinforced insulation working voltage; up to 1000 V<sub>RMS</sub> basic insulation working voltage.

#### UL

The Si858x is certified under UL1577 component recognition program. For more details, see File E257455.

Rated up to 6.0 kV $_{RMS}$ ,  $V_{ISO}$  isolation voltage for basic protection.

#### CQC

The Si858x is certified under GB4943.1-2011.

Rated up to 250 V<sub>RMS</sub> reinforced insulation working voltage at 5000 meters tropical climate.

#### Note:

1. Regulatory Certifications apply to >2.5 kV<sub>RMS</sub> rated devices which are production tested to 3.0 kV<sub>RMS</sub> for 1 sec. Regulatory Certifications apply to 3.75 kV<sub>RMS</sub> rated devices which are production tested to 4.5 kV<sub>RMS</sub> for 1 sec. Regulatory Certifications apply to 6.0 kV<sub>RMS</sub> rated devices which are production tested to 7.2 kV<sub>RMS</sub> for 1 sec. For more information, see Section1. Ordering Guide.

Table 4.4. Insulation and Safety-Related Specifications

Parameter	Symbol	Test Condition	Value WB SOIC-16	Unit
Nominal External Air Gap (Clearance)	CLR		8.0	mm
Nominal External Tracking (Creepage)	CRP		8.0	mm
Minimum Internal Gap (Internal Clearance)	DTI		0.036	mm
Tracking Resistance	CTI or PTI	IEC60112	600	V <sub>RMS</sub>
Erosion Depth	ED		0.019	mm
Resistance (Input-Output) <sup>1</sup>	RIO	Test voltage = 500 V	10 <sup>12</sup>	Ω
Capacitance (Input-Output) <sup>1</sup>	CIO	f = 1 MHz	2.0	pF
Input Capacitance <sup>2</sup>	CI		4.0	pF

- 1. To determine resistance and capacitance, the Si858x is converted into a 2-terminal device. Pins on Side A are shorted together to form the first terminal and pins on Side B are shorted together to form the second terminal. The parameters are then measured between these two terminals.
- 2. Measured from input pin to ground.

Table 4.5. IEC 60664-1 Ratings

Parameter	Test Condition	Specification WB SOIC-16
Basic Isolation Group	Material Group	1
	RateMains Voltages < 150 V <sub>RMS</sub>	I–IV
Installation Classification	RateMains Voltages < 300 V <sub>RMS</sub>	I–IV
Installation Classification	RateMains Voltages < 400 V <sub>RMS</sub>	I–III
	RateMains Voltages < 600 V <sub>RMS</sub>	I–III

Table 4.6. IEC 60747-17 Insulation Characteristics for Si858x <sup>1</sup>

Parameter	Symbol	Test Condition	Characteristic WB SOIC-16	Unit
Maximum Working Insulation Voltage	$V_{\text{IOWM}}$		1500	$V_{RMS}$
Maximum Repetitive Isolation Voltage	V <sub>IORM</sub>	Method b1  (VIORM x 1.875 = VPR, 100%  Production Test, tm = 1 sec, Partial Discharge < 5 pC)	2121	$V_{peak}$
Input to Output Test Voltage	V <sub>PR</sub>	Method b1 (V <sub>IORM</sub> x 1.875 = V <sub>PR</sub> , 100% Production Test, tm = 1 sec, Partial Discharge < 5 pC)	3977	V <sub>peak</sub>
Maximum Transient Isolation Voltage	V <sub>IOTM</sub>	t = 60 s	8000	V <sub>peak</sub>
Maximum Surge Isolation Voltage	V <sub>IOSM</sub>	Tested with 10400 V <sub>peak</sub> and 1.2 µs/50 µs profile	8000	$V_{peak}$
Maximum Impulse Voltage	V <sub>IOSM</sub>	Tested with 8000 V <sub>peak</sub> and 1.2 µs/50 µs profile	8000	$V_{peak}$
Pollution Degree		DIN VDE 0110	2	
Insulation Resistance	R <sub>S</sub>	TAMB = T <sub>S</sub> , V <sub>IO</sub> = 500 V	>10 <sup>9</sup>	Ω

<sup>1.</sup> Maintenance of the safety data is ensured by protective circuits. The Si858x provides a climate classification of 40/125/21.

Table 4.7. IEC Safety Limiting Values<sup>1</sup>

Parameter	Symbol	Test Condition	WB SOIC-16	Unit
Safety temperature	T <sub>S</sub>		150	°C
Safety input current	I <sub>S</sub>	θ <sub>JA</sub> = 55 °C/W	413	mA
Device power dissipation	P <sub>D</sub>	(WB SOIC-16), V <sub>DDA</sub> = 5.5 V, T <sub>J</sub> = 150 °C, T <sub>A</sub> = 25 °C	2.27	W

**Table 4.8. Thermal Characteristics** 

Parameter	Symbol	WB SOIC-16	Unit
IC junction-to-air thermal resistance	$\theta_{JA}$	55	°C/W

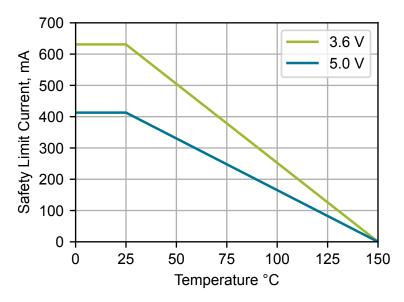


Figure 4.20. WB SOIC-16 Thermal Derating Curve (Dependence of Safety Limiting Current)

<sup>1.</sup> Maximum value allowed in the event of a failure. Refer to the thermal derating curve in Figure 4.20 WB SOIC-16 Thermal Derating Curve (Dependence of Safety Limiting Current) on page 18.

Table 4.9. Absolute Maximum Ratings<sup>1</sup>

Parameter	Symbol	Min	Max	Unit
Storage temperature	T <sub>STG</sub>	<b>–</b> 65	+150	°C
Junction temperature	TJ	_	+150	°C
Input supply voltage	VDD1, VDD2	-0.6	6.0	V
Voltage on any digital pin with respect to ground, Tx, TX_EN, Rx, RX_EN V5_EN	V <sub>IN</sub>	-0.5	VDD + 0.5	V
Bus fault protection		-30	30	V
Voltage on bus pin with respect to ground	VOC	-60	60	V
Receiver output current	Ю		10	mA
Lead solder temperature (10 s)		_	260	°C
	HBM, bus pins only		15	kV
	CDM, bus pins only		2	kV
ESD per JEDEC	HBM, all other pins		4	kV
	CDM, all other pins		1.5	kV
EOD AEO 0400	НВМ	_	4	kV
ESD per AEC-Q100	CDM	_	500	V
Maximum isolation (input-to-out- out, 1 sec)		_	6000	VRMS

<sup>1.</sup> Permanent device damage may occur if the absolute maximum ratings are exceeded. Functional operation should be restricted to the conditions as specified in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

# 5. Pinout Diagrams

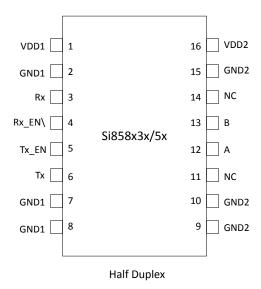


Figure 5.1. Pinout Diagram for Half Duplex Transceivers

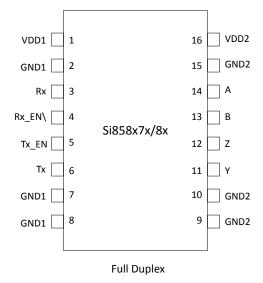


Figure 5.2. Pinout Diagram for Full Duplex Transceivers

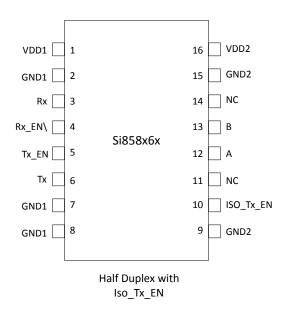


Figure 5.3. Pinout Diagram for Half Duplex with Isolated Tx\_EN

# 6. Pin Descriptions

Table 6.1. Pin Descriptions

Pin Name	Description		
Logic side			
VDD1	Logic side supply voltage		
NC	Not connected		
Tx	Driver input		
Tx_EN	Driver enable, with internal pull-up resistor. When open or driven high, driver is enabled.		
Rx_EN\	Rx enable (active low), with internal pull-down resistor. When open or driven low, the receiver is enabled.		
Rx	Receiver output		
GND1	Logic side supply ground		
Transceiver (bus) side			
GND2	Bus side supply ground		
Y, Z	Driver output bus pins for full duplex (Si858x7, Si858x8)		
A, B	Receiver input bus pins for full duplex (Si858x7, Si858x8) or driver/receiver bus pins for half duplex (Si858x3, Si858x5, Si858x6)		
ISO_Tx_EN	Isolated Tx_EN feedthrough		
VDD2	Bus side supply voltage, selectable through V5_EN pin		

# 7. Package Outline

The following figure illustrates the package details for the Si858x in a WB SOIC-16. The table lists the values for the dimensions shown in the illustration.

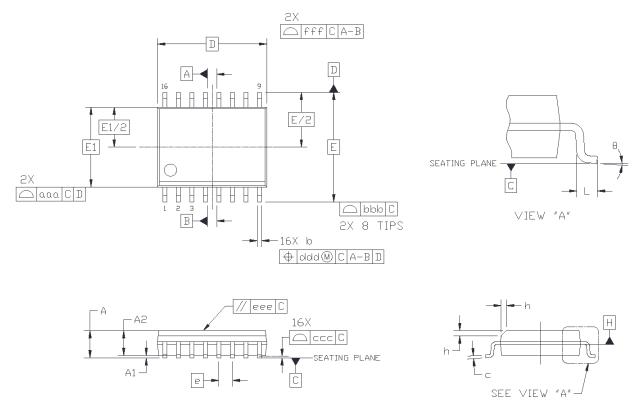


Figure 7.1. WB SOIC-16

**Table 7.1. Package Diagram Dimensions** 

Symbol	Millimeters	
	Min	Max
А	_	2.65
A1	0.10	0.30
A2	2.05	_
b	0.31	0.51
С	0.20	0.33
D	10.30 BSC	
E	10.30 BSC	
E1	7.50 BSC	
е	1.27 BSC	
L	0.40	1.27
h	0.25	0.75
θ	θ°	8°
ааа	_	0.10

Symbol	Millimeters	
	Min	Max
bbb	_	0.33
ссс	_	0.10
ddd	_	0.25
eee	_	0.10
fff	_	0.20

- 1. All dimensions shown are in millimeters (mm) unless otherwise noted.
- 2. Dimensioning and Tolerancing per ANSIY14.5M-1994.
- 3. Dimensioning and Tolerancing per ANSIY14.5M-1994.
- 4. All dimensions shown are in millimeters (mm) unless otherwise noted.

#### 8. Land Pattern

The following figure illustrates the recommended land pattern details for the Si858x in a WB SOIC-16. The table lists the values for the dimensions shown in the illustration.

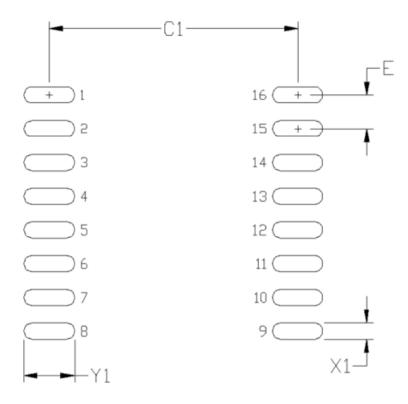


Figure 8.1. WB SOIC-16 PCB Land Pattern

Table 8.1. WB SOIC-16 Land Pattern Dimensions

Dimension	Feature	(mm)
C1	Pad Column Spacing	9.40
E	Pad Row Pitch	1.27
X1	Pad Width	0.60
Y1	Pad Length	1.90

- 1. This Land Pattern Design is based on IPC-7351 pattern SOIC127P1032X265-16AN for Density Level B (Median Land Protrusion).
- 2. All feature sizes shown are at Maximum Material Condition (MMC) and a card fabrication tolerance of 0.05 mm is assumed.

# 9. Top Marking

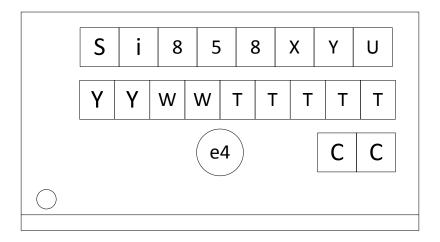


Table 9.1. WB SOIC-16 Top Marking Explanation

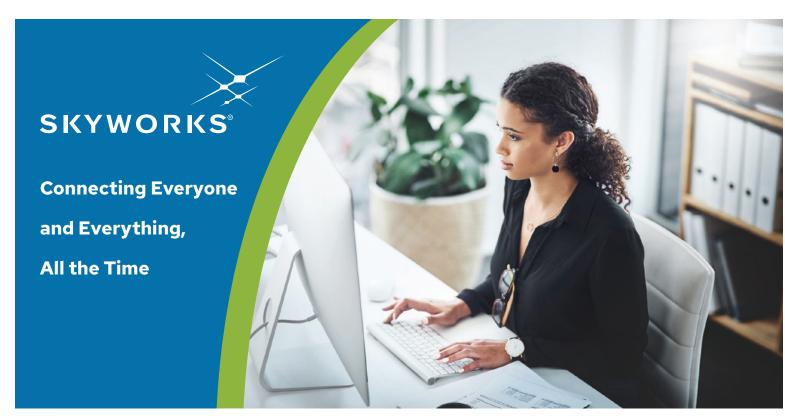
Line 1 Marking:	Base Part Number	Si858 = Isolated RS-485 Transceiver
	Ordering Options (See Ordering Guide for more information).	X = VDD2 nominal supply voltage:  • 3 = 3.3 V  • 5 = 5.0 V  Y = Transceiver type:  • 3 = 1 Mbps half duplex  • 5 = 10 Mbps half duplex  • 6 = 10 Mbps half duplex with isolated Tx_EN pin  • 7 = 1 Mbps full duplex  • 8 = 10 Mbps full duplex  U = Isolation rating:  • D = 5.0 kV
Line 2 Marking:	YY = Year WW = Workweek	Assigned by the assembly house. Corresponds to the year and workweek of the mold date.
	TTTTT = Mfg Code	Manufacturing code from assembly purchase order form.
Line 3 Marking:	Circle = 1.5 mm Diameter (Center-Justified)	"e4" Pb-Free Symbol
	Country of Origin ISO Code Abbreviation	TW = Taiwan

# 10. Revision History

# Revision 0.2

May, 2022

· Initial release.





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